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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Mitsuhiro Nakamura et al. Atty. Docket No. 075834.00079
Serial No.: 09/ 862,894 Group Art Unit: 2836
Filed: May 22, 2001 Examiner: Isabel Rodriguez
Invention: "PROTECTION CIRCUIT OF FIELD EFFECT TRANSISTOR
AND SEMICONDUCTOR DEVICE"

PRELIMINARY AMENDMENT ACCOMPANYING RCE

Commissioner for Patents
Mail Stop RCE
P.O. Box 1450
Alexandria, VA 22313-1450

S I R:

In response to the Office Action dated July 7, 2003, please amend the application as follows:

IN THE CLAIMS:

1. (Currently Amended) A protection circuit of a hetero-junction field effect transistor for protecting a gate electrode of the hetero-junction field effect transistor against surge breakdown, comprising:

a Schottky barrier diode array having a plurality of forward direction first diodes and reverse direction second diodes, the number of second diodes being equal to that of the first diodes, are cascade-connected,

wherein a gate electrode of the hetero-junction field effect transistor is grounded through the Schottky barrier diode array.

2. (Currently Amended) A protection circuit of a hetero-junction field effect transistor according to claim 1, wherein each diode of the diode array is formed as a Schottky

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